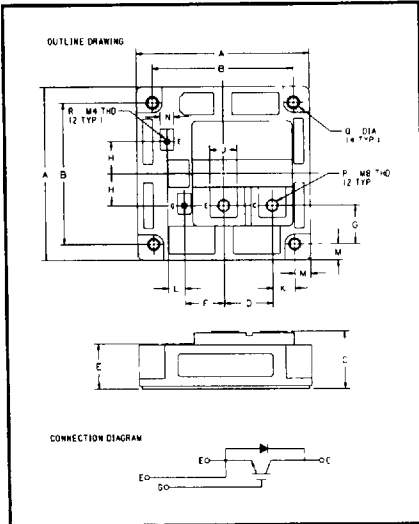


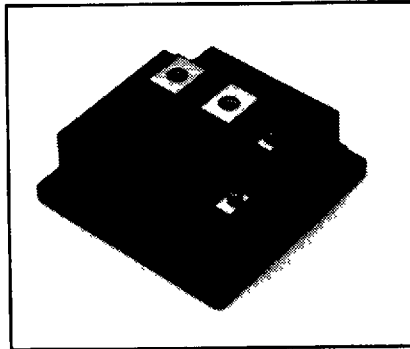
Powerex, Inc., 200 Hillis Street, Youngwood, Pennsylvania 15697-1800 (412) 925-7272
 Powerex, Europe, S.A. 428 Avenue G. Durand, BP107, 72003 Le Mans, France (43) 41.14.14

POWEREX INC

Single IGBTMOD™ Power Module 600 Amperes/1400 Volts



CM600HA-28
 Outline Drawing



CM600HA-28
 Single IGBTMOD™ Power Module
 600 Amperes/1400 Volts

Description:

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of one IGBT Transistor in a single configuration with a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- Low Drive Power
- Low $V_{CE(sat)}$
- Discrete Super-Fast Recovery (150ns) Free-Wheel Diode
- High Frequency Operation (15-20kHz)
- Isolated Baseplate for Easy Heat Sinking

Applications:

- AC Motor Control
- Motion/Servo Control
- UPS
- Welding Power Supplies
- Laser Power Supplies

Ordering Information:

Example: Select the complete part module number you desire from the table below

-i.e. CM600HA-28 is a 1400V (V_{CES}), 600 Ampere Single IGBTMOD™ Power Module.

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	600	28

Dimensions	Inches	Millimeters
A	4.49	114.0
B	3.66	93.0
C	1.5+0.0/-0.02	38.0+0.0/-0.5
D	1.26	32.0
E	1.18+0.0/-0.02	30.0+0.0/-0.5
F	1.02	26.0
G	1.00	25.5
H	0.83	21.0
J	0.71	18.0
K	0.57	14.5
L	0.43	11.0
M	0.41	10.5
N	0.35	9.0
P	M8 Metric	M8
Q	0.256 Dia.	Dia. 6.5
R	M4 Metric	M4

Powerex, Inc., 200 Hillis Street, Youngwood, Pennsylvania 15697-1800 (412) 925-7272
 Powerex, Europe, S.A. 428 Avenue G. Durand, BP107, 72003 Le Mans, France (43) 41.14.14

CM600HA-28
Single IGBTMOD™ Power Module
 600 Amperes/1400 Volts

Absolute Maximum Ratings, $T_j = 25\text{ °C}$ unless otherwise specified

Ratings	Symbol	CM600HA-28	Units
Junction Temperature	T_j	-40 to 150	°C
Storage Temperature	T_{stg}	-40 to 125	°C
Collector-Emitter Voltage (G-E SHORT)	V_{CES}	1400	Volts
Gate-Emitter Voltage	V_{GES}	±20	Volts
Collector Current	I_C	600	Amperes
Peak Collector Current	I_{CM}	1200*	Amperes
Diode Forward Current	I_{FM}	600	Amperes
Diode Forward Surge Current	I_{FM}	1200*	Amperes
Power Dissipation	P_d	5600	Watts
Max. Mounting Torque M8 Terminal Screws	-	72	in-lb
Max. Mounting Torque M6 Mounting Screws	-	26	in-lb
Module Weight (Typical)	-	990	Grams
V Isolation	V_{RMS}	2500	Volts

* Pulse width and repetition rate should be such that device junction temperature does not exceed the device rating

Static Electrical Characteristics, $T_j = 25\text{ °C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0V$	-	-	2.0	mA
Gate Leakage Current	I_{GES}	$V_{GE} = V_{GES}, V_{CE} = 0V$	-	-	0.5	μA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 60mA, V_{CE} = 10V$	3.5	5.0	6.5	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 600A, V_{GE} = 15V$	-	-	5.0**	Volts
		$I_C = 600A, V_{GE} = 15V, T_j = 150\text{ °C}$	-	-	5.0**	Volts
Total Gate Charge	Q_G	$V_{CC} = 800V, I_C = 600A, V_{GS} = 15V$	-	8500	-	nC
Diode Forward Voltage	V_{FM}	$I_E = 600A, V_{GS} = 0V$	-	-	2.8	Volts

** Pulse width and repetition rate should be such that device junction temperature rise is negligible

Dynamic Electrical Characteristics, $T_j = 25\text{ °C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	C_{ies}		-	-	132	nF
Output Capacitance	C_{oes}	$V_{GE} = 0V, V_{CE} = 10V, f = 1MHz$	-	-	34	nF
Reverse Transfer Capacitance	C_{res}		-	-	3.4	nF
Resistive	Turn-on Delay Time	$t_{d(on)}$	-	-	3000	ns
Load	Rise Time	t_r	-	-	1200	ns
Switch Times	Turn-off Delay Time	$t_{d(off)}$	-	-	2000	ns
	Fall Time	t_f	-	-	800	ns
Diode Reverse Recovery Time	t_{rr}	$I_E = 600A, di_E/dt = -1200A/\mu s$	-	-	400	ns
Diode Reverse Recovery Charge	Q_{rr}	$I_E = 600A, di_E/dt = -1200A/\mu s$	-	18	-	μC

Thermal and Mechanical Characteristics, $T_j = 25\text{ °C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per IGBT	-	-	0.023	°C/W
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per Free Wheel Diode	-	-	0.044	°C/W
Contact Thermal Resistance	$R_{th(c-f)}$	Per Module	-	-	0.023	°C/W